MC74HC541A

Octal 3-State Noninverting Buffer/Line Driver/Line Receiver

High–Performance Silicon–Gate CMOS

The MC74HC541A is identical in pinout to the LS541. The device inputs are compatible with Standard CMOS outputs. External pull–up resistors make them compatible with LSTTL outputs.

The HC541A is an octal noninverting buffer/line driver/line receiver designed to be used with 3–state memory address drivers, clock drivers, and other bus–oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active–low output enables.

The HC541A is similar in function to the HC540A, which has inverting outputs.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates

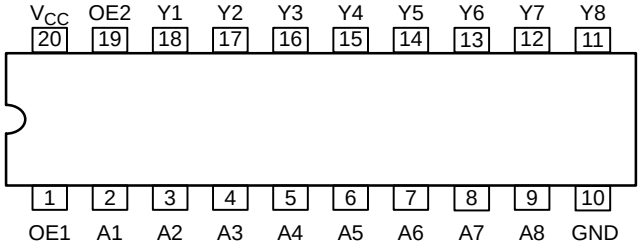


Figure 1. Pinout: 20–Lead Packages (Top View)

FUNCTION TABLE

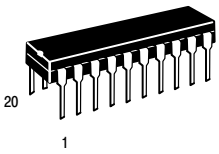
Inputs			Output Y
OE1	OE2	A	
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

X = Don't Care
Z = High Impedance

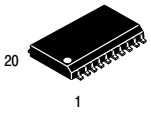
ON Semiconductor

http://onsemi.com

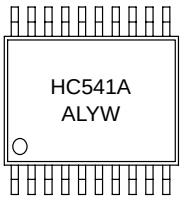
MARKING DIAGRAMS



PDIP–20
N SUFFIX
CASE 783



SO–20
DW SUFFIX
CASE 751D



TSSOP–20
DT SUFFIX
CASE 948E

A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74HC541AN	PDIP–20	1440/Box
MC74HC541ADW	SOIC–WIDE	38/Rail
MC74HC541ADWR2	SOIC–WIDE	1000/Reel
MC74HC541ADT	TSSOP–20	75/Rail
MC74HC541ADTR2	TSSOP–20	2500/Reel

© Semiconductor Components Industries, LLC, 2001

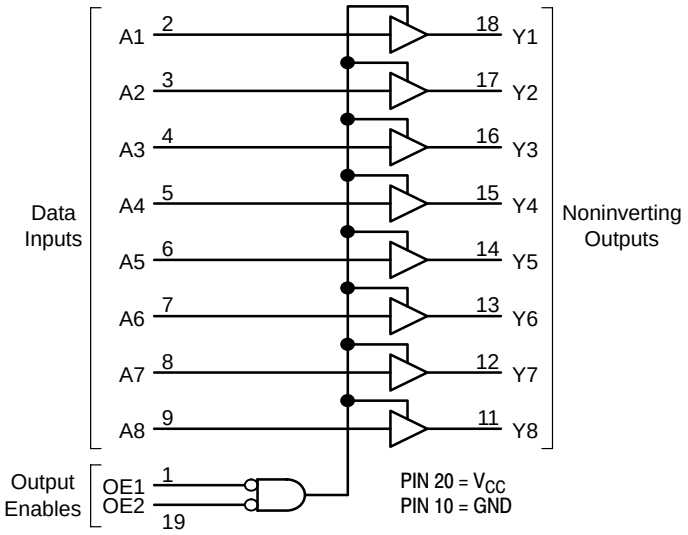


Figure 2. Logic Diagram

MAXIMUM RATINGS (Note 1)

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_I	DC Input Voltage		$-0.5 \le V_I \le +0.5$	V
V_O	DC Output Voltage	(Note 2)	$-0.5 \le V_O \le +0.5$	V
I_{IK}	DC Input Diode Current		±20	mA
I_{OK}	DC Output Diode Current		±35	mA
I_O	DC Output Sink Current		±35	mA
I_{CC}	DC Supply Current per Supply Pin		±75	mA
I_{GND}	DC Ground Current per Ground Pin		±75	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	PDIP SOIC TSSOP	67 96 128	°C/W
P_D	Power Dissipation in Still Air at 85°C	PDIP SOIC TSSOP	750 500 450	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 30% – 35%	UL–94–VO (0.125 in)	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	> 4000 > 300 > 1000	V
$I_{Latch–Up}$	Latch–Up Performance	Above V_{CC} and Below GND at 85°C (Note 6)	±300	mA

1. Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum–rated conditions is not implied.
2. I_O absolute maximum rating must be observed.
3. Tested to EIA/JESD22–A114–A.
4. Tested to EIA/JESD22–A115–A.
5. Tested to JESD22–C101–A.
6. Tested to EIA/JESD78.
7. For high frequency or heavy load considerations, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage	(Referenced to GND)	2.0	6.0	V
V_{IN}, V_{OUT}	DC Input Voltage, Output Voltage	(Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature Range, All Package Types		−55	+125	°C
t_r, t_f	Input Rise/Fall Time (Figure 3)	V_{CC} = 2.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V	0 0 0	1000 500 400	ns

8. Unused inputs may not be left open. All inputs must be tied to a high–logic voltage level or a low–logic input voltage level.

DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V_{CC} V	Guaranteed Limit −55°C to 25°C	Guaranteed Limit ≤85°C	Guaranteed Limit ≤125°C	Unit
V_{IH}	Minimum High–Level Input Voltage	V_{OUT} = 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V_{IL}	Maximum Low–Level Input Voltage	V_{OUT} = V_{CC} – 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V_{OH}	Minimum High–Level Output Voltage	V_{IN} = V_{IL} $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V_{IN} = V_{IL} $\|I_{OUT}\| \le 3.6$ mA $\|I_{OUT}\| \le 6.0$ mA $\|I_{OUT}\| \le 7.8$ mA	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V_{OL}	Maximum Low–Level Output Voltage	V_{IN} = V_{IH} $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V_{IN} = V_{IH} $\|I_{OUT}\| \le 3.6$ mA $\|I_{OUT}\| \le 6.0$ mA $\|I_{OUT}\| \le 7.8$ mA	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I_{IN}	Maximum Input Leakage Current	V_{IN} = V_{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum Three–State Leakage Current	Output in High Impedance State V_{IN} = V_{IL} or V_{IH} V_{OUT} = V_{CC} or GND	6.0	±0.5	±5.0	±10.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA	6.0	4	40	160	μA

9. Information on typical parametric values can be found in the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit −55°C to 25°C	Guaranteed Limit ≤85°C	Guaranteed Limit ≤125°C	Unit
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	80 30 18 15	100 40 23 20	120 55 28 25	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 4 and 6)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
t_{PZL}, t_{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 4 and 6)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 5)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C_{IN}	Maximum Input Capacitance		10	10	10	pF
C_{OUT}	Maximum Three–State Output Capacitance (High Impedance State Output)		15	15	15	pF

10. For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V_{CC} = 5.0 V, V_{EE} = 0 V	
C_{PD}	Power Dissipation Capacitance (Per Buffer) (Note 11)	35	pF

11. Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

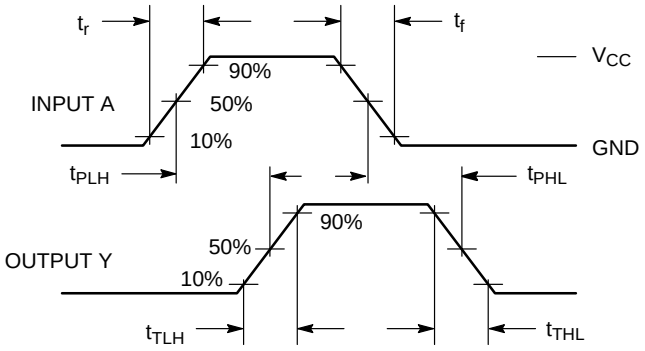


Figure 3. Switching Waveform

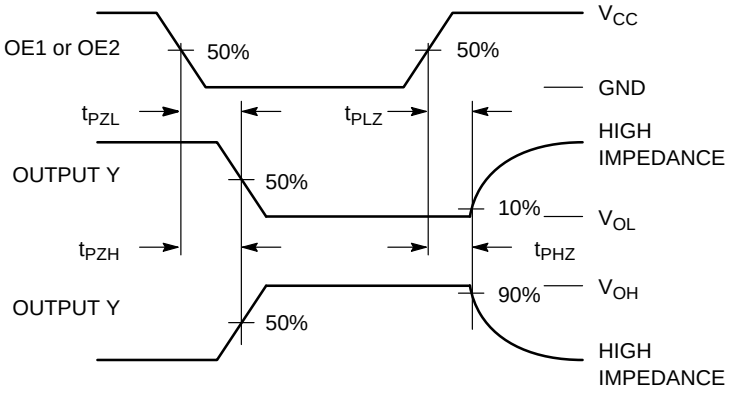
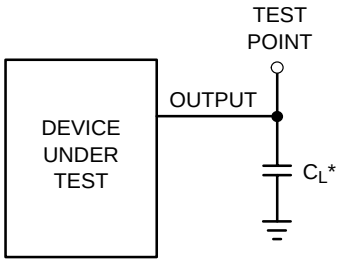
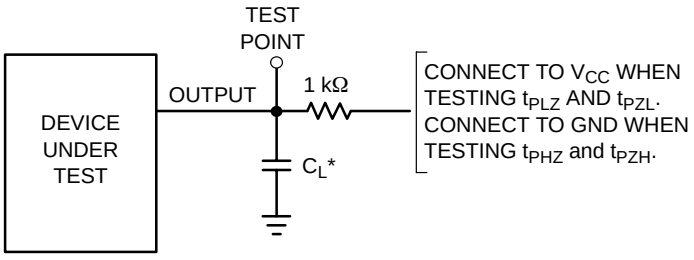


Figure 4. Switching Waveform



*Includes all probe and jig capacitance

Figure 5. Test Circuit



*Includes all probe and jig capacitance

Figure 6. Test Circuit

PIN DESCRIPTIONS

INPUTS

A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9)

Data input pins. Data on these pins appear in non–inverted form on the corresponding Y outputs, when the outputs are enabled.

CONTROLS

OE1, OE2 (PINS 1, 19)

Output enables (active–low). When a low voltage is applied to both of these pins, the outputs are enabled and the device functions as an non–inverting buffer. When a high voltage is applied to either input, the outputs assume the high impedance state.

OUTPUTS

Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11)

Device outputs. Depending upon the state of the output enable pins, these outputs are either non–inverting outputs or high–impedance outputs.

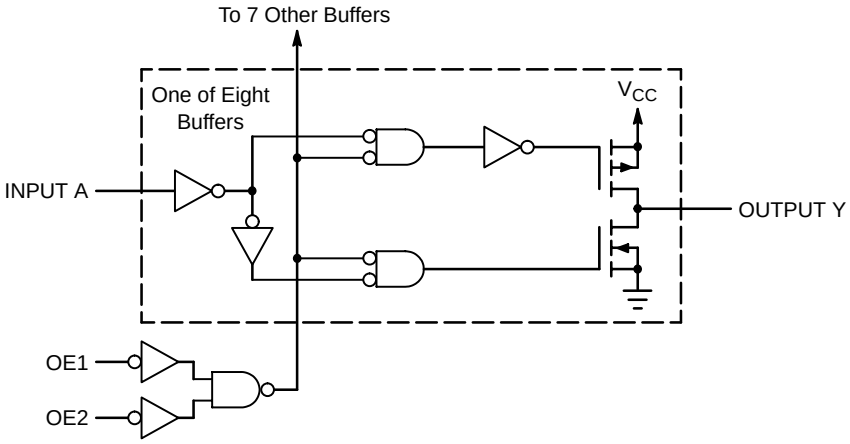
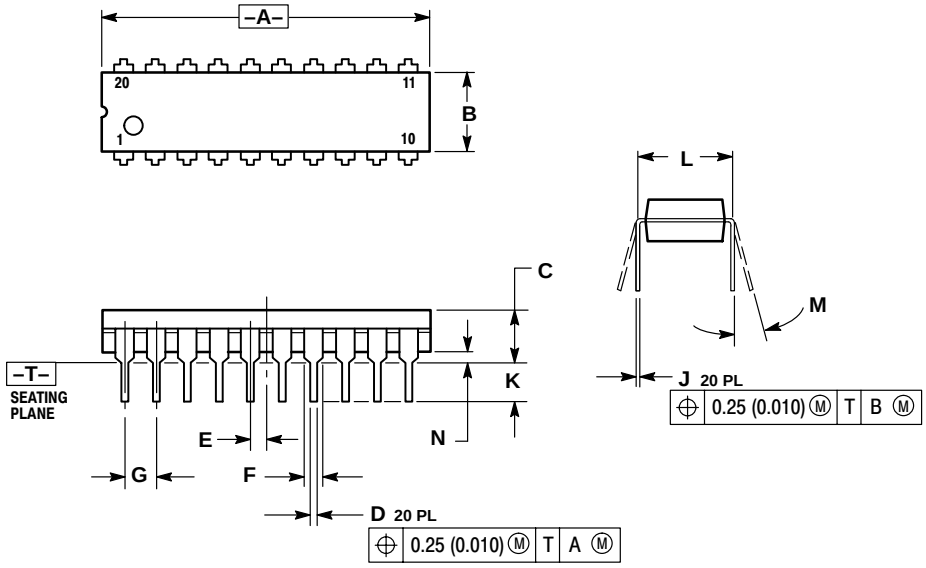


Figure 7. Logic Detail

PACKAGE DIMENSIONS

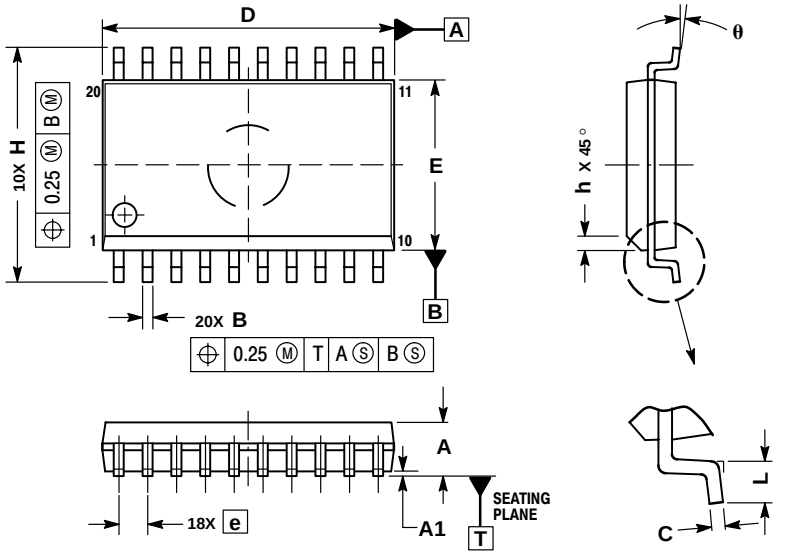
PDIP
N SUFFIX
PLASTIC DIP PACKAGE
CASE 738–03
ISSUE E



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.010	1.070	25.66	27.17
B	0.240	0.260	6.10	6.60
C	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050 BSC		1.27 BSC	
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

SO–20
DW SUFFIX
CASE 751D–05
ISSUE F

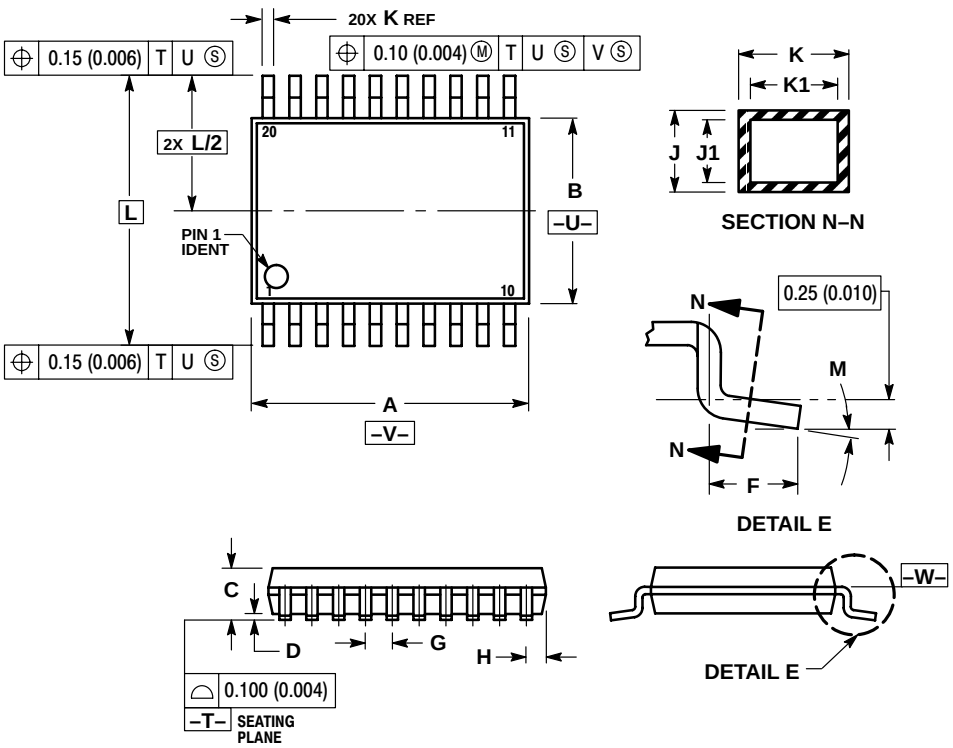


NOTES:
1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS	
DIM	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

PACKAGE DIMENSIONS

TSSOP
DT SUFFIX
20 PIN PLASTIC TSSOP PACKAGE
CASE 948E–02
ISSUE A



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada
Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com
Fax Response Line: 303–675–2167 or 800–344–3810 Toll Free USA/Canada

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support
German Phone: (+1) 303–308–7140 (Mon–Fri 2:30pm to 7:00pm CET)
Email: ONlit–german@hibbertco.com
French Phone: (+1) 303–308–7141 (Mon–Fri 2:00pm to 7:00pm CET)
Email: ONlit–french@hibbertco.com
English Phone: (+1) 303–308–7142 (Mon–Fri 12:00pm to 5:00pm GMT)
Email: ONlit@hibbertco.com

EUROPEAN TOLL–FREE ACCESS*: 00–800–4422–3781
*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:
Spanish Phone: 303–308–7143 (Mon–Fri 8:00am to 5:00pm MST)
Email: ONlit–spanish@hibbertco.com
Toll–Free from Mexico: Dial 01–800–288–2872 for Access – then Dial 866–297–9322

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support
Phone: 1–303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time)
Toll Free from Hong Kong & Singapore:
001–800–4422–3781
Email: ONlit–asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center
4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031
Phone: 81–3–5740–2700
Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.